

# PN120S

## Silicon NPN Phototransistor

For optical control systems

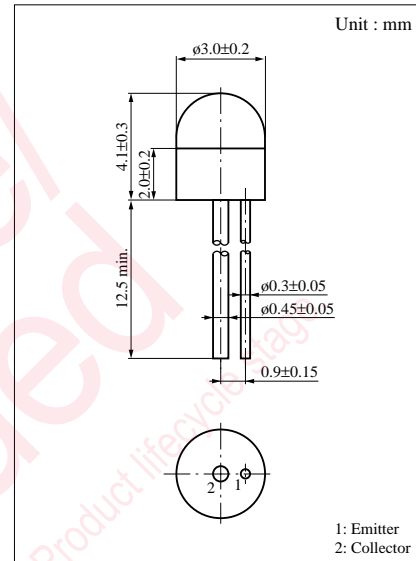
Can be combined with LN62S to form an optical controller

### ■ Features

- High sensitivity
- Wide directional sensitivity for easy use
- Fast response :  $t_r, t_f = 3 \mu s$  (typ.)
- Small size ( $\phi 3$ ) ceramic package

### ■ Absolute Maximum Ratings ( $T_a = 25^\circ C$ )

Parameter	Symbol	Ratings	Unit
Collector to emitter voltage	$V_{CEO}$	30	V
Emitter to collector voltage	$V_{ECO}$	5	V
Collector current	$I_C$	20	mA
Collector power dissipation	$P_C$	50	mW
Operating ambient temperature	$T_{opr}$	-25 to +85	$^\circ C$
Storage temperature	$T_{stg}$	-30 to +100	$^\circ C$

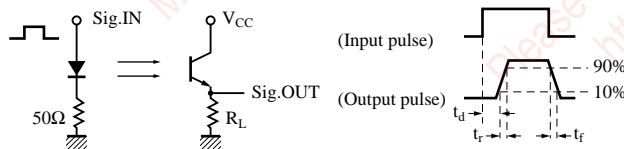


### ■ Electro-Optical Characteristics ( $T_a = 25^\circ C$ )

Parameter	Symbol	Conditions	min	typ	max	Unit
Dark current	$I_{CEO}$	$V_{CE} = 10V$		5	500	nA
Collector photo current	$I_{CE(L)1}$	$V_{CE} = 10V, L = 2 lx^{*1}$	3	*3		$\mu A$
	$I_{CE(L)2}$	$V_{CE} = 10V, L = 500 lx^{*1}$		*3		mA
Peak sensitivity wavelength	$\lambda_p$	$V_{CE} = 10V$		800		nm
Acceptance half angle	$\theta$	Measured from the optical axis to the half power point		50		deg.
Response time	$t_r, t_f^{*2}$	$V_{CC} = 10V, I_{CE(L)} = 5mA, R_L = 100\Omega$		3		$\mu s$
Collector saturation voltage	$V_{CE(sat)}$	$I_{CE(L)} = 1mA, L = 1000 lx^{*1}$		0.2	0.5	V

\*1 Measurements were made using a tungsten lamp (color temperature  $T = 2856K$ ) as a light source.

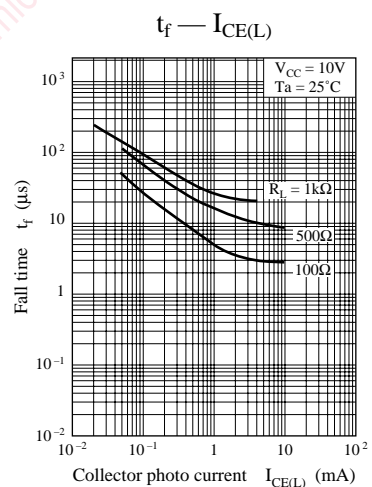
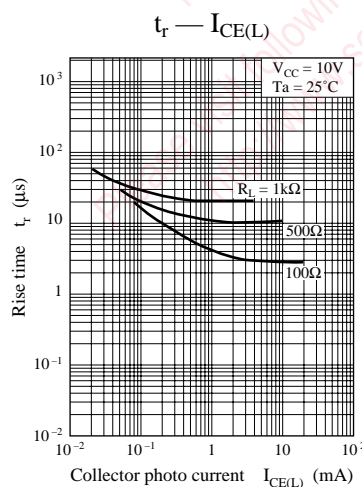
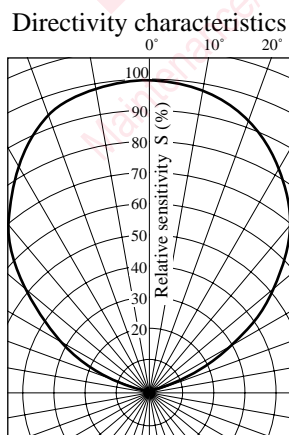
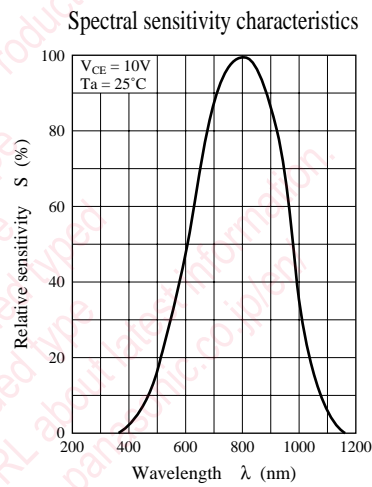
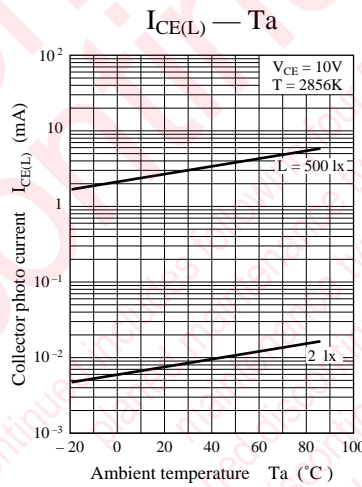
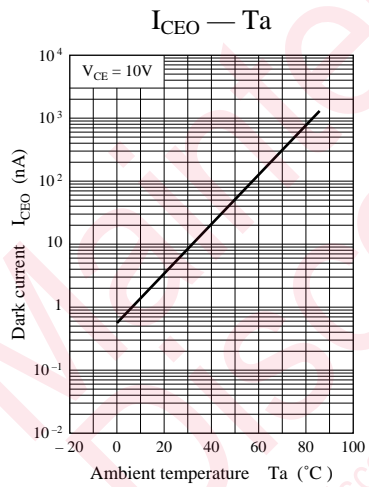
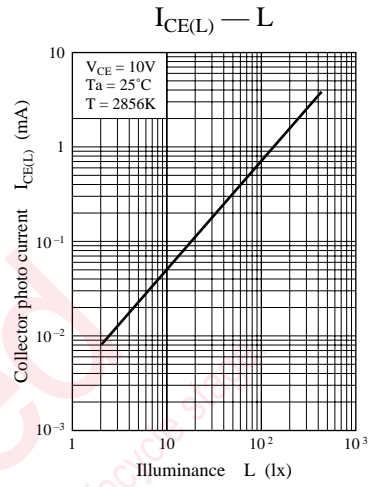
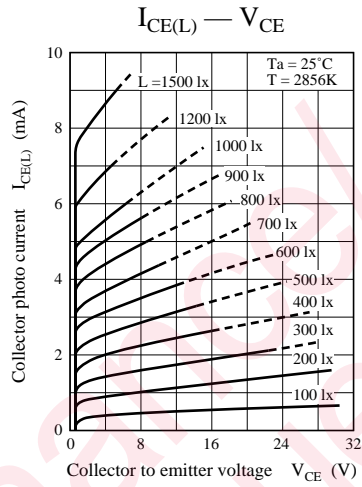
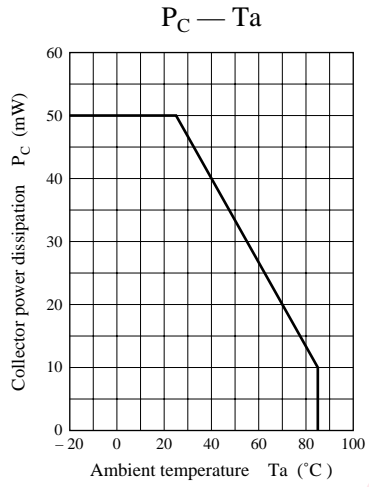
\*2 Switching time measurement circuit



$t_d$ : Delay time  
 $t_r$ : Rise time (Time required for the collector photo current to increase from 10% to 90% of its final value)  
 $t_f$ : Fall time (Time required for the collector photo current to decrease from 90% to 10% of its initial value)

\*3  $I_{CE(L)}$  Classifications

Class	QL	RL	SL
$I_{CE(L)1}$ ( $\mu A$ )	3 to 16	10 to 30	>24
$I_{CE(L)2}$ (mA)	5 typ.	6 typ.	8 typ.



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